

DUAL 4-INPUT NAND GATE

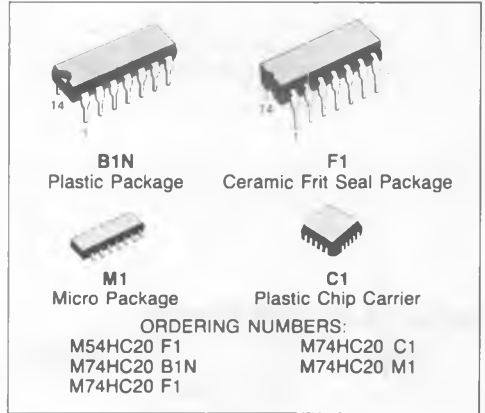
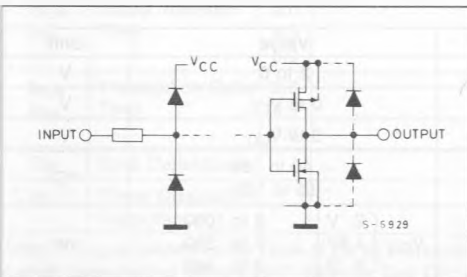
- **HIGH SPEED**
 $t_{PD} = 10 \text{ ns (TYP.) at } V_{CC} = 5V$
- **LOW POWER DISSIPATION**
 $I_{CC} = 1 \mu A \text{ (MAX.) at } T_A = 25^\circ C$
- **HIGH NOISE IMMUNITY**
 $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (MIN.)}$
- **OUTPUT DRIVE CAPABILITY**
 10 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE**
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 6V$
- **PIN AND FUNCTION COMPATIBLE**
 WITH 54/74LS20

DESCRIPTION

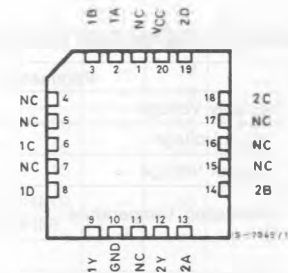
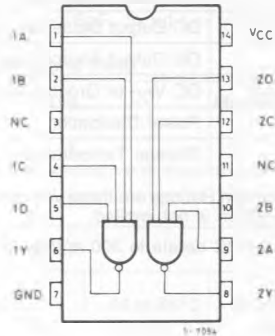
The M54/74HC20 is a high speed CMOS DUAL 4-INPUT NAND GATE fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

The internal circuit is composed of 3 stages including buffered output, which gives high noise immunity and a stable output. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT

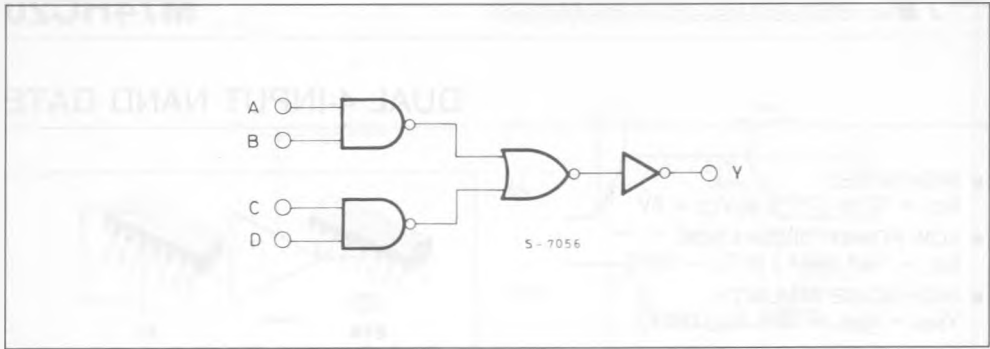


PIN CONNECTIONS (top view)



NC =
 No Internal
 Connection

LOGIC DIAGRAM (per Gate)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	- 0.5 to 7	V
V_I	DC Input Voltage	- 0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	- 0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	- 65 to 150	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500 mW: $\cong 65^{\circ}C$ derate to 300 mW by 10 mW/ $^{\circ}C$: $65^{\circ}C$ to $85^{\circ}C$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_A	Operating Temperature	74HC Series 54HC Series	$^{\circ}C$
		- 40 to 85 - 55 to 125	
t_r, t_f	Input Rise and Fall Time	V_{CC} $\begin{cases} 2 \text{ V} & 0 \text{ to } 1000 \\ 4.5 \text{ V} & 0 \text{ to } 500 \\ 6 \text{ V} & 0 \text{ to } 400 \end{cases}$	ns

DC SPECIFICATIONS

Symbol	Parameter	V _{CC}	Test Condition		T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0 4.5 6.0			1.5 3.15 4.2	— — —	— — —	1.5 3.15 4.2	— — —	1.5 3.15 4.2	— — —	V
V _{IL}	Low Level Input Voltage	2.0 4.5 6.0			— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V
V _{OH}	High Level Output Voltage	2.0	V _I	I _O	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	1.9 4.4 5.9	— — —	V
		4.5 6.0	V _{IH} or V _{IL}	- 20 μA								
		4.5 6.0	V _{IH} or V _{IL}	- 4.0 mA - 5.2 mA								
V _{OL}	Low Level Output Voltage	2.0	V _{IH} or V _{IL}	20 μA	— — —	0 0 0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
		4.5 6.0										
		4.5 6.0										
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND		—	—	± 0.1	—	± 1	—	± 1	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND		—	—	1	—	10	—	20	μA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V, T_A = 25°C, C_L = 15pF, Input t_r = t_f = 6ns)

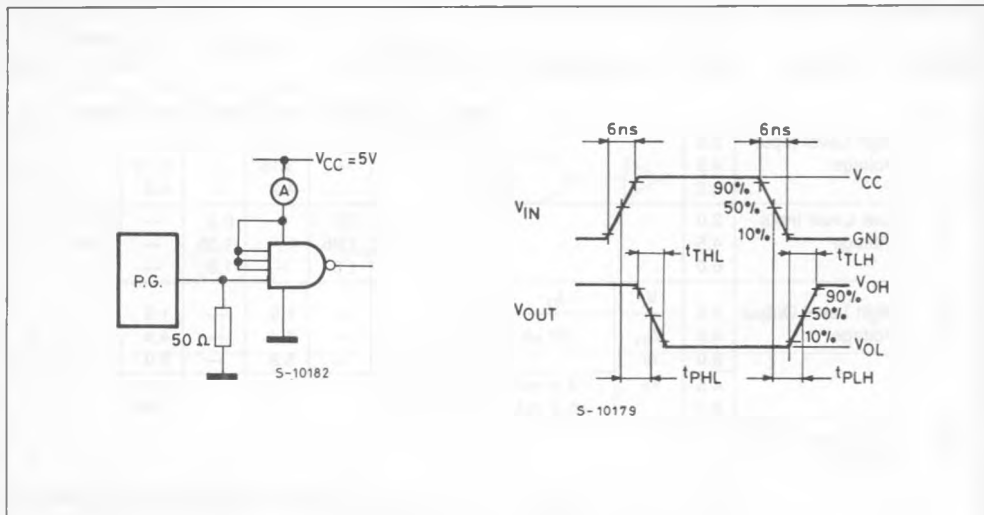
Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
t _{TLH} t _{THL}	Output Transition Time		4	8	ns
t _{PLH} t _{PHL}	Propagation Delay Time		11	18	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input t_r = t_f = 6ns)

Symbol	Parameter	V _{CC}	Test Condition		T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0 4.5 6.0			— — —	30 8 7	75 15 13	— — —	95 19 16	— — —	110 22 19	ns
t _{PLH} t _{PHL}	Propagation Delay Time	2.0 4.5 6.0			— — —	44 11 9	90 18 15	— — —	115 23 20	— — —	135 27 23	ns
C _{IN}	Input Capacitance				—	5	10	—	10	—	10	pF
C _{PD} (*)	Power Dissipation Capacitance				—	28	—	—	—	—	—	pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)

SWITCHING CHARACTERISTICS TEST CIRCUIT



TEST CIRCUIT I_{CC} (Opr.)

